

Figure 1 –GPC as a function of a) $Mo(CO)_6$ pulse time, b) O_3 pulse time, c) $Mo(CO)_6$ purge time, and d) O_3 purge time, as determined by in-situ spectroscopic ellipsometry (SE).



Figure 3 –MoO₃ film thickness mapping on a 100 mm wafer, as determined by ex-situ SE. Variations in the uniformity have been limited to 3%, indicating the self-limiting nature of the process in agreement with Fig. 1. The thickness is slightly higher near the $Mo(CO)_6$ gas inlet (top-right).



Figure 5 – Angle-resolved XPS measurements after at-H reduction of MoO_3 for 30 min at a) 150 °C and b) 350 °C.



Figure 2 –GPC as a function of process temperature, as determined by in situ SE. The sharper increase of GPC above 185 °C is attributed to $Mo(CO)_6$ decomposition.



Figure 4 – Mo3d peak positions from XPS for a) pure MoO₃, b) after reduction of MoO₃ at 150 °C for 30 min in at-H, and c) after reduction of MoO₃ at 350 °C for 30 min in at-H.

References:

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